

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	44	"5854494"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:27
L3	93	"5426605"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:42
L4	1	JP "09504657"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:46
L5	1	JP "06209092"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:51
L6	2	JP "11040758"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:51
L7	0	EP "0724777"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:54
L8	0	EP "0588402"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:55

L9	0	EP0588402	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:55
L10	0	EP "0588402"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:55
S54	3	"20050174845"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S55	2	WO near2 "9607300"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S56	1	1996-160638.NRAN.	DERWENT	ADJ	ON	2010/06/04 18:10
S57	18	"5195010"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S58	5633	heat\$3 with silicon with (voltage or current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S59	317	(chang\$3 or alter\$3 or convert\$3) with silicon with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S60	2	(chang\$3 or alter\$3 or convert\$3) with silicon with (current or voltage) with heat\$3 with (source and drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

S61	15	(chang\$3 or alter\$3 or convert\$3) with ((poly silicon) or (polycrystalline silicon) or (poly\$1S)) with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S62	10	(chang\$3 or alter\$3 or convert\$3) with (SiGe or (silicon germanium)) with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S63	662	(MURAKAMI near2 SHIGERU).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S64	29	(YAMAGATA near2 YASUJI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S65	4485	(257/16,49,52,59).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S66	724	(257/64,68).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S67	1281	(257/770-772).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S68	390	(438/153).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S69	1654	(438/166).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S70	3009	(438/238-239).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S71	1476	(438/478).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S72	3	"20020126108"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S73	13807	((write near2 once) memory) or (WOM)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

S74	12417	(semiconductor (film or material)) same ((amorphous silicon) or (a \$1silicon) or (a\$1Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S75	63	S73 and S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S76	10427	((write near2 once) memory) or (one time programmable) or (OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S77	24817	(semiconductor (film or material)) same ((amorphous silicon) or (a \$1silicon) or (a\$1Si) or (SiGe) or (Silicon Germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S78	238	S76 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S79	291	((gate or dielectric or insulat \$3) and (semiconductor)) and (((write near2 once) memory) or (one time programmable) or (OTP)). ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S80	8	((thin film transistor) or (thinfilm transistor) or TFT) and S79	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S81	1	jp "56044198"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11

S82	185	"20030198077" "20050098811" "20050194645" "20060054894" "20060175648" "5850090" "5994730" "6384439" "6465828" "6555420" "6576948" "6583490" "6690031" "6958740" "7113420" "7368343"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S83	53854	voltage same increas\$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S84	51204	((write near2 once) memory) or (one time programmable) or (OTP)) and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S85	2657	((thin film transistor) or (thinfilm transistor) or TFT) and S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S86	136	memory.ti. and S85	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S87	1278	((apply\$3 or programm\$4 or operat\$3) near3 voltage) same (alter\$3 or chang\$3 or convert\$3) same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S88	229	((thin film transistor) or (thinfilm transistor) or TFT) and S87	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S89	10	((write near2 once) memory) or (one time programmable) or (OTP)) and S88	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11

S90	2702	voltage same increase\$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S91	20	((write near2 once) memory) or (one time programmable) or (OTP)) and S90	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S92	1	10/573527	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/03/31 12:54

4/ 4/ 2011 11:00:52 AM

H:\ EAST\ Workspaces\ 10573527_final.wsp